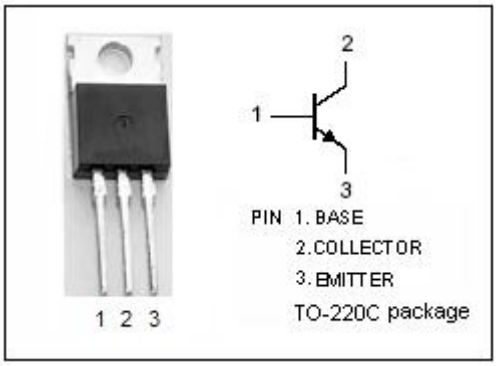
SPTECH Silicon NPN Power Transistor

DESCRIPTION

- Collector–Emitter Sustaining Voltage
  : $V_{CEO(SUS)}$ = 400V(Min.)
- Collector Saturation Voltage
  : $V_{CE(sat)}$ = 2.0(Max) @ I_C= 5.0A
- Switching Time
  : t_f= 0.9 μ s(Max.)@ I_C= 5.0A



APPLICATIONS

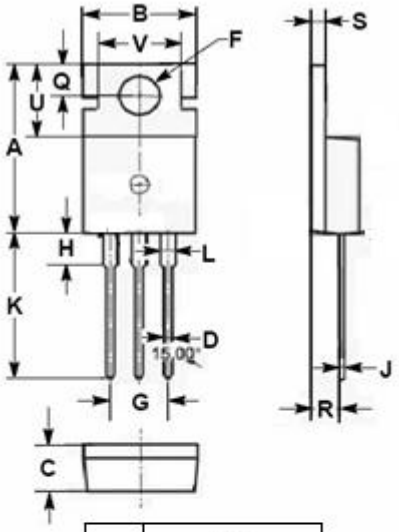
- Designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220V switchmode applications such as switching regulators,inverters,Motor controls,Solenoid/Relay drivers and deflection circuits.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	700	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	9	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-peak	16	A
I_B	Base Current	4	A
I_{BM}	Base Current-Peak	8	A
I_E	Emitter Current	12	A
I_{EM}	Emitter Current-Peak	24	A
P_C	Collector Power Dissipation T_C=25℃	80	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.56	℃/W
$R_{th\ j\text{-}a}$	Thermal Resistance,Junction to Ambient	62.5	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

SPTECH Silicon NPN Power Transistor

ELECTRICAL CHARACTERISTICS

T_C =25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 10mA; I_B= 0	400			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 2A ;I_B= 0.4A			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 5A ;I_B= 1A T_C= 100℃			2.0 3.0	V
$V_{CE(sat)-3}$	Collector-Emitter Saturation Voltage	I_C= 8A ;I_B= 2A			3.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	I_C= 2A ;I_B= 0.4A			1.2	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	I_C= 5A ;I_B= 1A T_C= 100℃			1.6 1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 700V; I_E=0 T_C= 125℃			0.1 1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 9V; I_C= 0			0.1	mA
h_{FE-1}	DC Current Gain	I_C= 2A; V_{CE}= 5V	8		40	
h_{FE-2}	DC Current Gain	I_C= 5A; V_{CE}= 5V	5		30	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5 A; V_{CE}= 10V;	4			MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test} = 0.1MHz		80		pF
Switching Times; Resistive Load						
t_d	Storage Time	I_C= 5A; V_{CC}= 125V; I_{B1}= I_{B2}= 1A; t_p= 25 μ s; Duty Cycle≤ 1%			0.1	μ s
t_r	Fall Time				1.5	μ s
t_s	Storage Time				3.0	μ s
t_f	Fall Time				0.7	μ s